FDMC007N30D

MOSFET, Dual N-Channel, POWERTRENCH®

Q1: 30 V, 11.6 mΩ; Q2: 30 V, 6.4 mΩ

General Description

This device includes two specialized N−Channel MOSFETs in a dual Power33 (3mm × 3mm MLP) package. The switch node has been internally connected to enable easy placement and routing of synchronous buck converters. The control MOSFET (Q1) and synchronous MOSFET (Q2) have been designed to provide optimal power efficiency.

Features

Q1: N−Channel

- Max $r_{DS(on)}$ = 11.6 mΩ at V_{GS} = 10 V, I_D = 10 A
- Max $r_{DS(on)}$ = 13.3 mΩ at V_{GS} = 4.5 V, I_D = 9 A

Q1: N−Channel

- Max $r_{DS(on)}$ = 6.4 mΩ at V_{GS} = 10 V, I_D = 16 A
- Max $r_{DS(on)}$ = 7.0 mΩ at V_{GS} = 4.5 V, I_D = 15 A
- RoHS Compliant

Applications

- Mobile Computing
- Mobile Internet Devices
- General Purpose Point of Load

MOSFET MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Symbol	Parameter	Q1	Q2	Unit
V_{DS}	Drain to Source Voltage	30	30	V
V_{GS}	Gate to Source Voltage (Note 4)	±12	±12	V
I_D	Drain Current: – Continuous, T_C = 25°C (Note 6) – Continuous, T_C = 100°C (Note 6) – Continuous, T_A = 25°C (Note 1a) – Pulsed (Note 5)	 29 18 10 (Note 1a) 113	 46 29 16 (Note 1b) 302	A
E_{AS}	Single Pulse Avalanche Energy (Note 3)	24	54	mJ
P_D	Power Dissipation for Single Operation: T_A = 25°C T_A = 25°C	 1.9 (Note 1a) 0.7 (Note 1c)	 2.5 (Note 1b) 1.0 (Note 1d)	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	−55 to +150		°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

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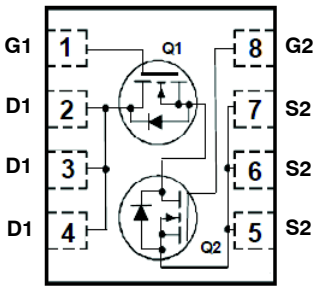
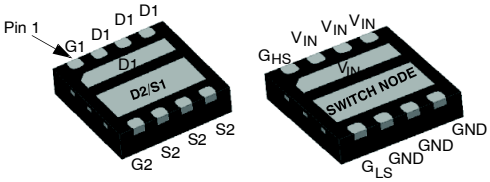


Dual N-Channel MOSFET

Bottom



WDFN8 3x3
CASE 511DE

MARKING DIAGRAM

$Y	= ON Semiconductor Logo
&Z	= Assembly Plant Code
&2	= Data Code (Year & Week)
&K	= Lot
FDMC7N30D	= Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

PACKAGE MARKING AND ORDERING INFORMATION

Device Marking	Device	Package	Quantity
FDMC7N30D	FDMC007N30D	WDFN−8 (Power 33)	3000/Tape&Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

THERMAL CHARACTERISTICS

Symbol	Parameter	Q1	Q2	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case	8.2	6.1	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	65 (Note 1a)	50 (Note 1b)	
		180 (Note 1c)	125 (Note 1d)	

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

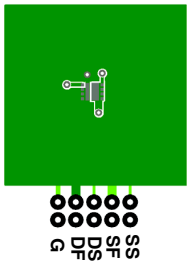
Symbol	Parameter	Test Condition	Type	Min	Typ	Max	Unit
OFF CHARACTERISTICS							
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250 μA, V_{GS} = 0 V I_D = 250 μA, V_{GS} = 0 V	Q1 Q2	30 30			V
ΔBV_{DSS} /ΔT_J	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25°C I_D = 250 μA, referenced to 25°C	Q1 Q2		15 16		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 24 V, V_{GS} = 0 V	Q1 Q2			1 1	μA
I_{GSS}	Gate to Source Leakage Current, Forward	V_{GS} = ±12 V, V_{DS} = 0 V	Q1 Q2			±100 ±100	nA
ON CHARACTERISTICS							
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 250 μA V_{GS} = V_{DS}, I_D = 250 μA	Q1 Q2	1.0 1.0	1.3 1.8	3.0 3.0	V
$\Delta V_{GS(th)}$ /ΔT_J	Gate to Source Threshold Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25°C I_D = 250 μA, referenced to 25°C	Q1 Q2		−4 −4		mV/°C
$r_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10 V, I_D = 10 A V_{GS} = 4.5 V, I_D = 9 A V_{GS} = 10 V, I_D = 10 A, T_J = 125°C	Q1		7.7 8.9 10.8	11.6 13.3 16.3	mΩ
$r_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10 V, I_D = 16 A V_{GS} = 4.5 V, I_D = 15 A V_{GS} = 10 V, I_D = 16 A, T_J = 125°C	Q2		4.4 5.4 6.2	6.4 7.0 9.0	mΩ
g_{FS}	Forward Transconductance	V_{DD} = 5 V, I_D = 10 A V_{DD} = 5 V, I_D = 16 A	Q1 Q2		46 70		S
DYNAMIC CHARACTERISTICS							
C_{iss}	Input Capacitance	V_{DS} = 15 V, V_{GS} = 0 V, f = 1 MHz	Q1 Q2		792 1685	1110 2360	pF
C_{oss}	Output Capacitance		Q1 Q2		230 467	325 655	pF
C_{rss}	Reverse Transfer Capacitance		Q1 Q2		20 36	30 50	pF
R_g	Gate Resistance		Q1 Q2	0.1 0.1	2.0 1.2	4.0 2.4	Ω

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted) (continued)

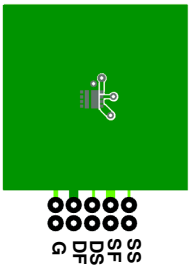
Symbol	Parameter	Test Condition	Type	Min	Typ	Max	Unit
SWITCHING CHARACTERISTICS							
$t_{d(on)}$	Turn-On Delay Time	Q1 V_{DD} = 15 V, I_D = 10 A, V_{GS} = 10 V, R_{GEN} = 6 Ω Q2 V_{DD} = 15 V, I_D = 16 A, V_{GS} = 10 V, R_{GEN} = 6 Ω	Q1 Q2		7 10	14 20	ns
t_r	Rise Time		Q1 Q2		2 3	10 10	ns
$t_{d(off)}$	Turn-Off Delay Time		Q1 Q2		19 24	33 39	ns
t_f	Fall Time		Q1 Q2		2 3	10 10	ns
$Q_{g(TOT)}$	Total Gate Charge	V_{GS} = 0 V to 10 V, Q1 V_{DD} = 15 V, I_D = 10 A	Q1 Q2		12 24	17 34	nC
		V_{GS} = 0 V to 4.5 V, Q1 V_{DD} = 15 V, I_D = 10 A	Q1 Q2		5.5 11	7.7 16	nC
Q_{gs}	Gate to Source Charge	Q2 V_{DD} = 15 V, I_D = 16 A	Q1 Q2		1.7 4.4		nC
Q_{gd}	Gate to Drain “Miller” Charge		Q1 Q2		1.3 2.7		nC
DRAIN−SOURCE DIODE CHARACTERISTICS							
V_{SD}	Source−Drain Diode Forward Voltage	V_{GS} = 0 V, I_S = 10 A (Note 2) V_{GS} = 0 V, I_S = 1.5 A (Note 2) V_{GS} = 0 V, I_S = 16 A (Note 2) V_{GS} = 0 V, I_S = 2 A (Note 2)	Q1 Q1 Q2 Q2		0.85 0.75 0.83 0.73	1.2 1.2 1.2 1.2	V
t_{rr}	Reverse Recovery Time	Q1 I_F = 10 A, di/dt = 100 A/μs	Q1 Q2		17 27	31 42	ns
Q_{rr}	Reverse Recovery Charge	Q2 I_F = 16 A, di/dt = 100 A/μs	Q1 Q2		5 10	10 20	nC

NOTES:

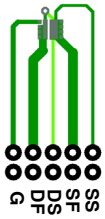
1. $R_{\theta JA}$ is determined with the device mounted on a 1 in^2 pad 2 oz copper pad on a 1.5 × 1.5 in. board of FR−4 material. $R_{\theta CA}$ is determined by the user’s board design.



a. 65 °C/W when mounted on a 1 in^2 pad of 2 oz copper.



b. 50 °C/W when mounted on a1 in^2 pad of 2 oz copper.



c. 180 °C/W when mounted on a minimum pad of 2 oz copper.

d. 125 °C/W when mounted on a minimum pad of 2 oz copper.

2. Pulse Test: Pulse Width < 300 uS, Duty cycle < 2.0%.
3. Q1: E_{AS} of 24 mJ is based on starting T_J = 25°C, L = 3 mH, I_{AS} = 4 A, V_{DD} = 30 V, V_{GS} = 10 V. 100% tested at L = 0.1 mH, I_{AS} = 13 A.
   Q2: E_{AS} of 54 mJ is based on starting T_J = 25°C, L = 3 mH, I_{AS} = 6 A, V_{DD} = 30 V, V_{GS} = 10 V. 100% tested at L = 0.1 mH, I_{AS} = 22 A.
4. As an N−ch device, the negative Vgs rating is for low duty cycle pulse occurrence only. No continuous rating is implied.
5. Pulsed Id please refer to Figure 11 and Figure. 24 SOA graph for more details.
6. Computed continuous current limited to Max Junction Temperature only, actual continuous current will be limited by thermal & electro−mechanical application board design.

TYPICAL CHARACTERISTICS (Q1 N−CHANNEL)

(T_J = 25°C unless otherwise noted)

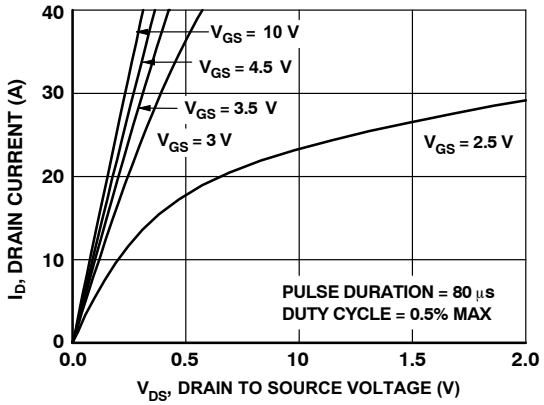


Figure 1. On Region Characteristics

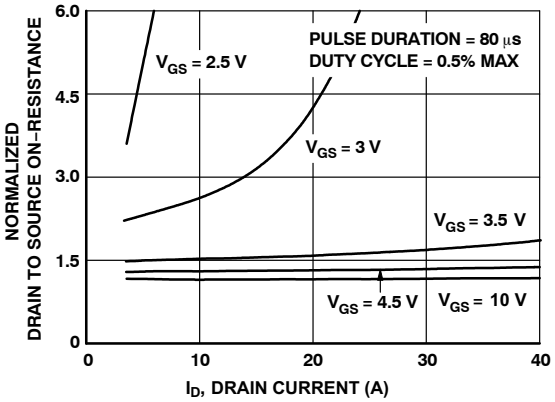


Figure 2. Normalized On−Resistance vs. Drain Current and Gate Voltage

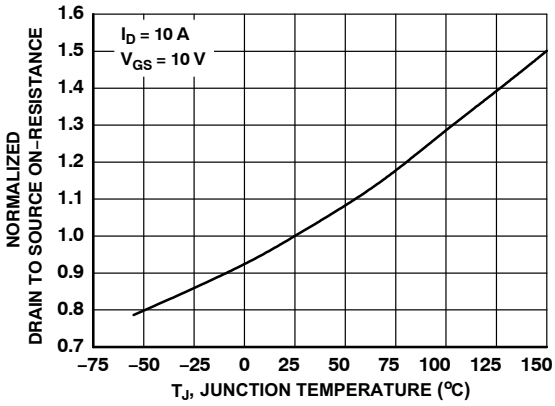


Figure 3. Normalized On Resistance vs. Junction Temperature

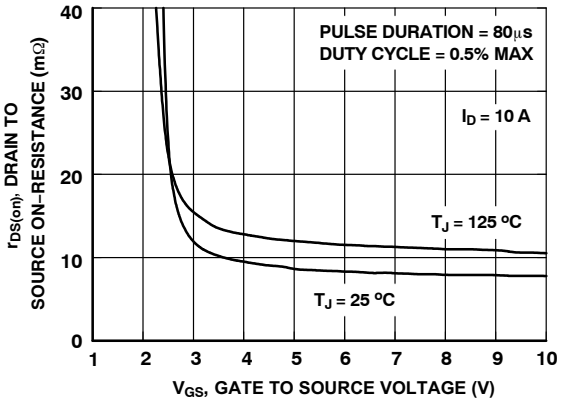


Figure 4. On−Resistance vs. Gate to Source Voltage

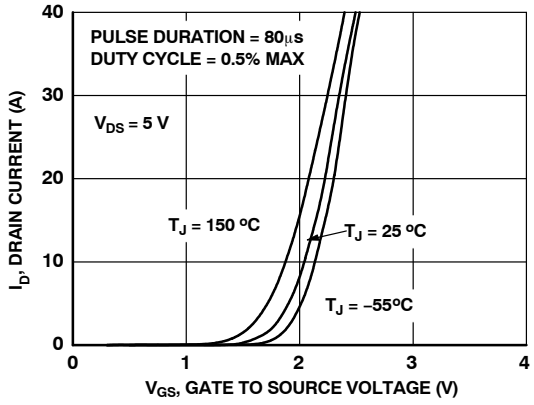


Figure 5. Transfer Characteristics

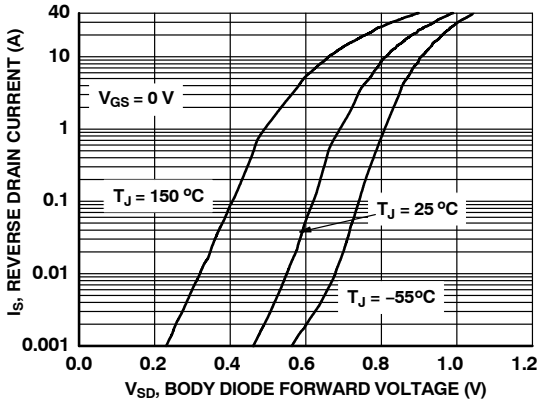


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

TYPICAL CHARACTERISTICS (Q1 N−CHANNEL) (continued)

(T_J = 25°C unless otherwise noted)

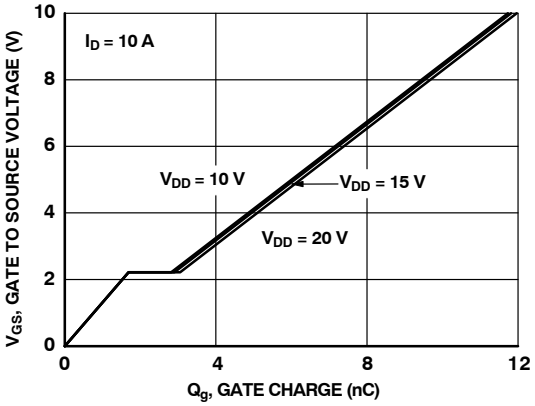


Figure 7. Gate Charge Characteristics

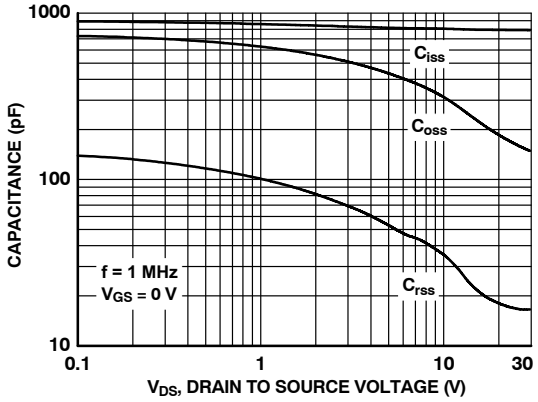


Figure 8. Capacitance vs. Drain to Source Voltage

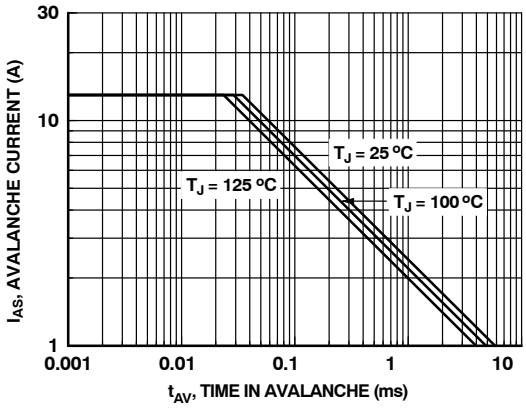


Figure 9. Unclamped Inductive Switching Capability

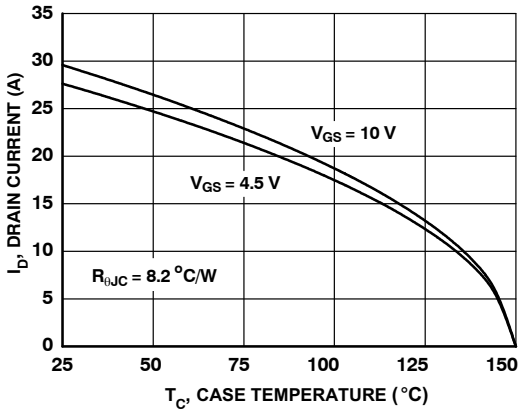


Figure 10. Maximum Continuous Drain Current vs. Case Temperature

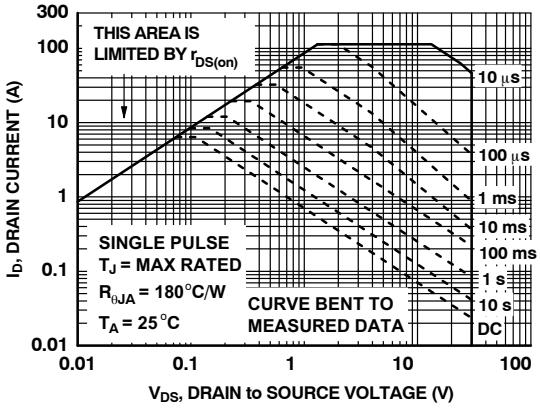


Figure 11. Forward Bias Safe Operating Area

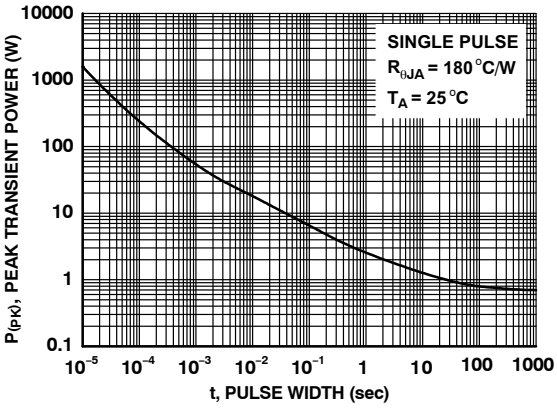


Figure 12. Single Pulse Maximum Power Dissipation

TYPICAL CHARACTERISTICS (Q1 N−CHANNEL) (continued)

(T_J = 25°C unless otherwise noted)

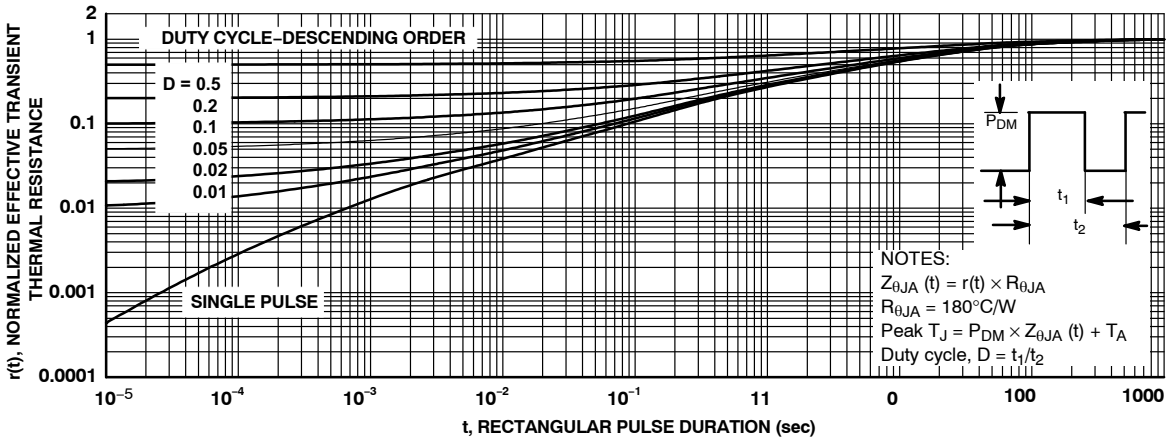


Figure 13. Junction−to−Ambient Transient Thermal Response Curve

TYPICAL CHARACTERISTICS (Q2 N−CHANNEL)

(T_J = 25°C unless otherwise noted)

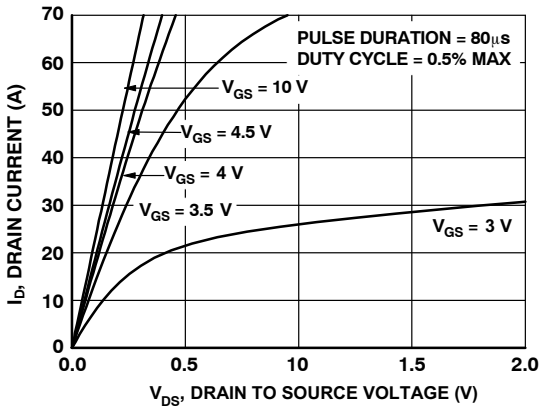


Figure 14. On Region Characteristics

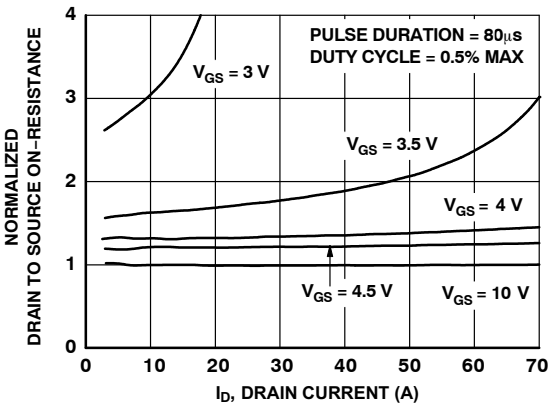


Figure 15. Normalized On−Resistance vs. Drain Current and Gate Voltage

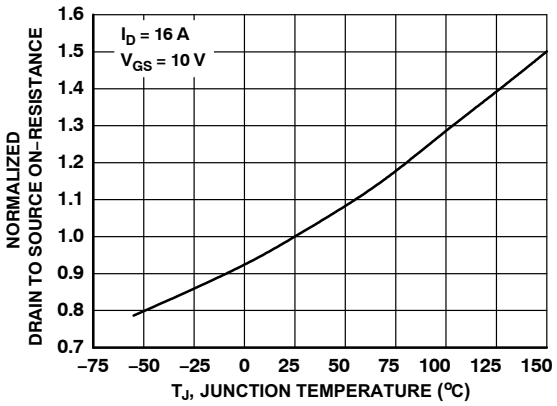


Figure 16. Normalized On Resistance vs. Junction Temperature

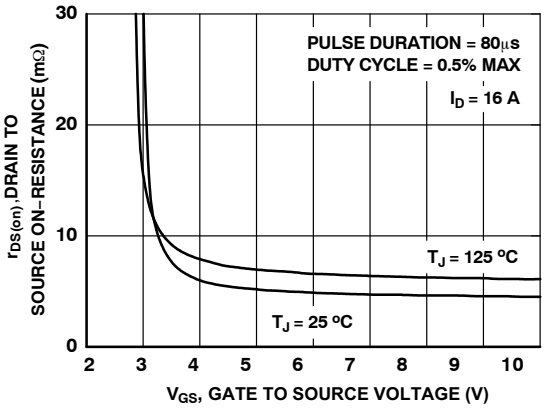


Figure 17. On−Resistance vs. Gate to Source Voltage

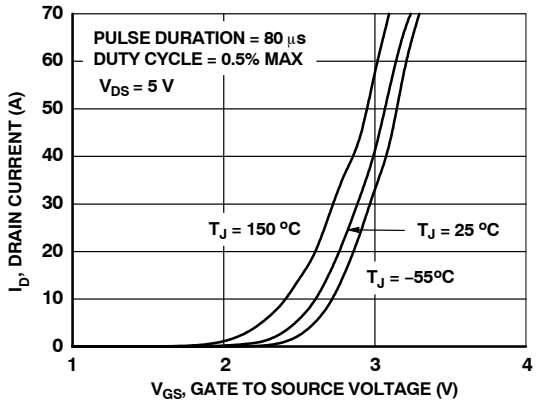


Figure 18. Transfer Characteristics

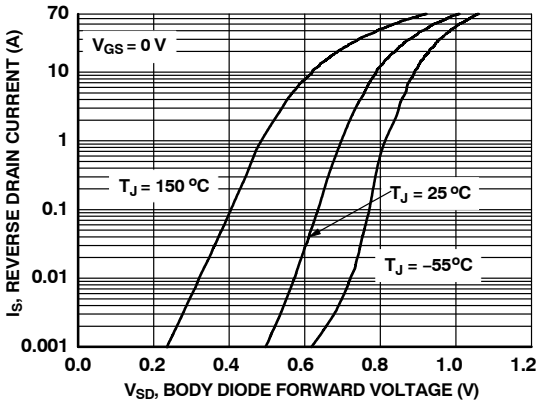


Figure 19. Source to Drain Diode Forward Voltage vs. Source Current

TYPICAL CHARACTERISTICS (Q2 N−CHANNEL) (continued)

(T_J = 25°C unless otherwise noted)

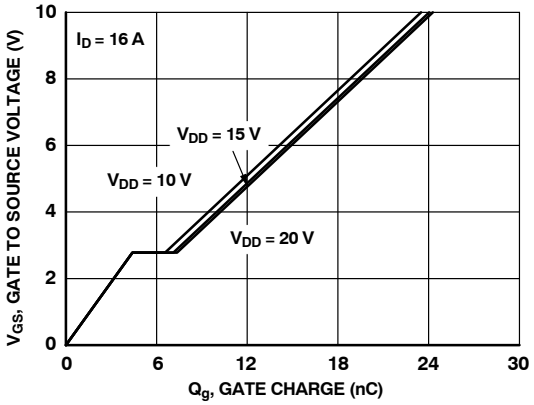


Figure 20. Gate Charge Characteristics

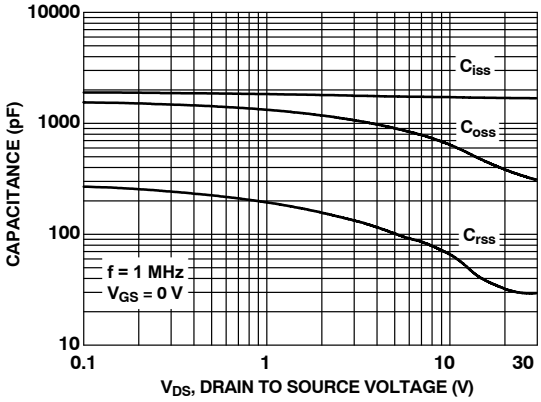


Figure 21. Capacitance vs. Drain to Source Voltage

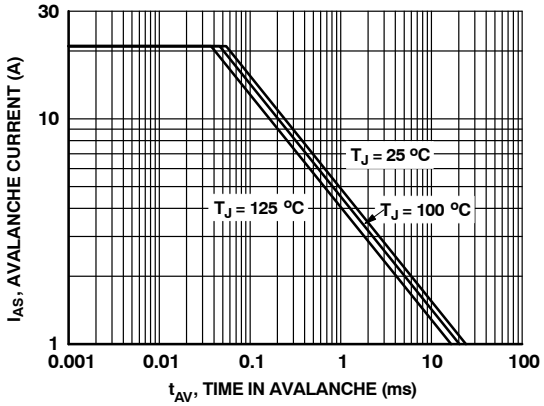


Figure 22. Unclamped Inductive Switching Capability

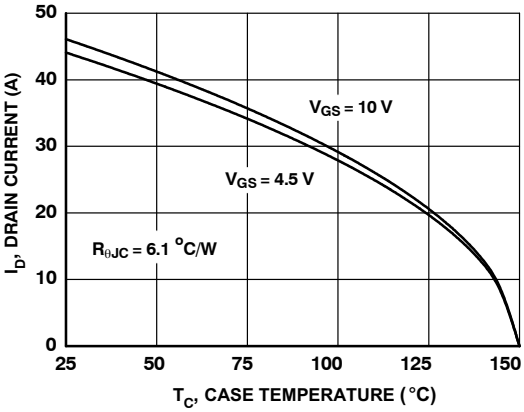


Figure 23. Maximum Continuous Drain Current vs. Case Temperature

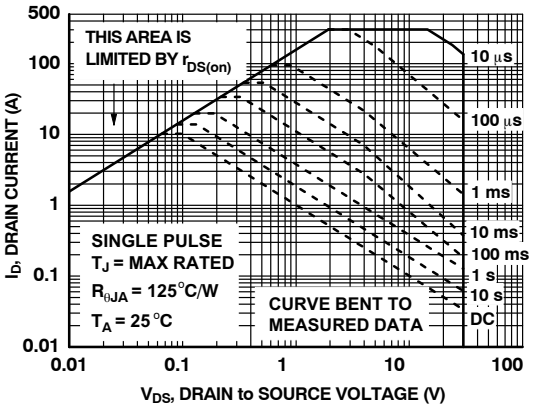


Figure 24. Forward Bias Safe Operating Area

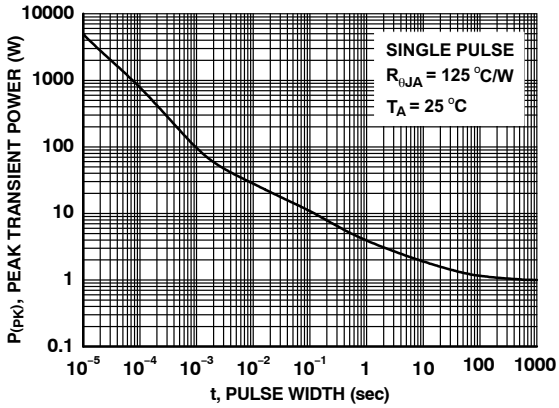


Figure 25. Single Pulse Maximum Power Dissipation

TYPICAL CHARACTERISTICS (Q2 N−CHANNEL) (continued)

(T_J = 25°C unless otherwise noted)

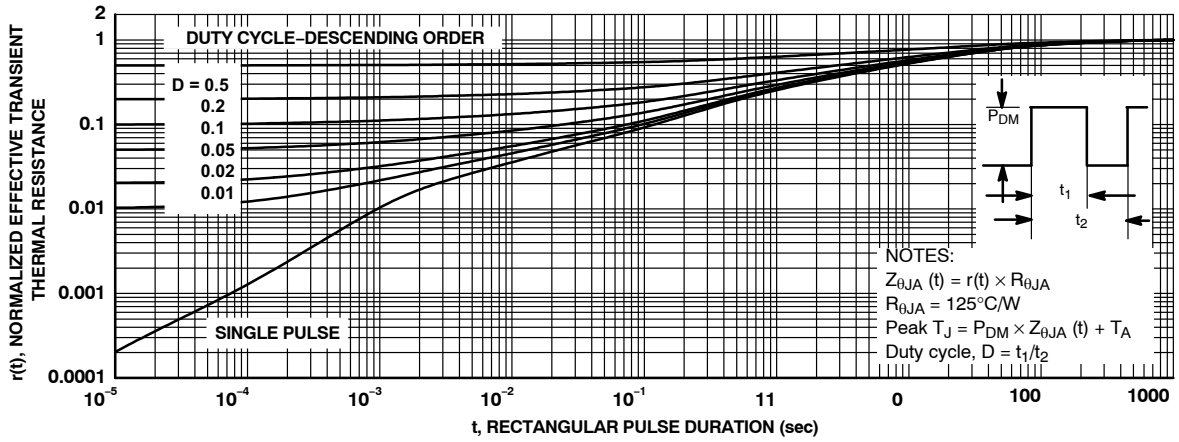


Figure 26. Junction−to−Ambient Transient Thermal Response Curve

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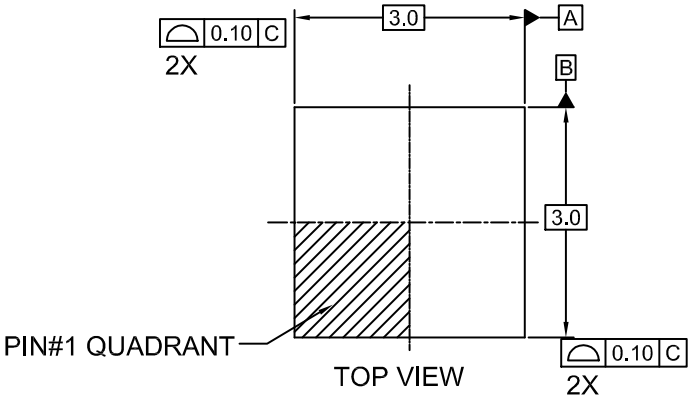
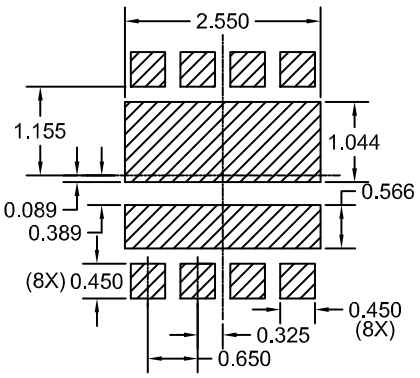
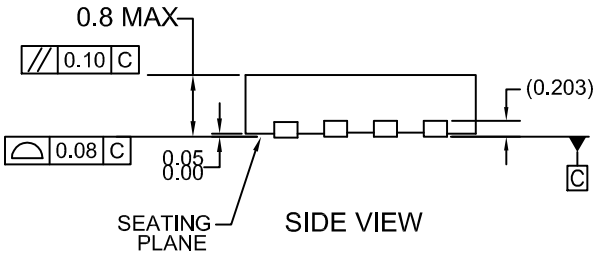
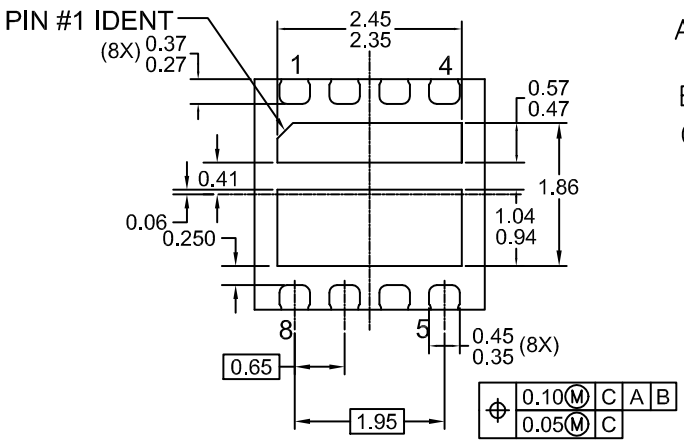
DATE 31 AUG 2016





RECOMMENDED LAND PATTERN





BOTTOM VIEW

NOTES:

A. DOES NOT CONFORM TO JEDEC REGISTRATION MO−229
B. DIMENSIONS ARE IN MILLIMETERS.
C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994

ISSUE	REVISION	DATE
O	RELEASED FOR PRODUCTION FROM FAIRCHILD MLP08N TO ON SEMICONDUCTOR. REQ. BY B. MARQUIS.	31 AUG 2016

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
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